

SEMICONDUCTOR MEMORY DEVICE

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Abstract of JP2002163899

PROBLEM TO BE SOLVED: To provide a semiconductor memory device which can dramatically reduce the time of the shipment test, which can lower producing cost, and which is effective when applied to general-purpose memory devices of larger capacity.

SOLUTION: The memory cell array 10 is divided to the banks or cell array units. This memory cell array 10 has a self-test functioning circuit 20 at each bank or at cell array units. Each of this self-test functioning circuit 20 can be controlled independently, and at each of this circuit 20, a comparing tool 25 compares the test output data and the expected value data. This tool 25 is equipped according to the number of output bits of the bank or cell array units.

